

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor structure comprising:
a semiconductor substrate; and
a Langmuir-Blodgett chemically amplified photoresist, including a non-ionic photoacid generator bonded to the hydrophobic region of an amphipathic molecule, formed over said semiconductor substrate.
2. (Original) The structure of claim 1 wherein said photoresist includes a non-ionic photoacid generator.
3. (Original) The structure of claim 2 wherein said photoacid generator is MDT.
4. (Original) The structure of claim 2 wherein said photoacid generator is NIT.
5. (Original) The structure of claim 1 wherein said photoresist is 193 nanometer photoresist.
6. (Original) The structure of claim 1 wherein said photoresist is 248 nanometer photoresist.
7. (Currently Amended) A method comprising:
forming a Langmuir-Blodgett chemically amplified photoresist over a semiconductor substrate, said photoresist including a non-ionic photoacid generator bonded to the hydrophobic region of an amphipathic molecule.
8. (Original) The method of claim 7 including a non-ionic photoacid generator in said photoresist.
9. (Original) The method of claim 8 including MDT as said photoacid generator.

10. (Original) The method of claim 8 including NIT as said photoacid generator.
11. (Original) The method of claim 7 including forming a 193 nanometer photoresist.
12. (Original) The method of claim 7 including forming a 248 nanometer photoresist.
13. (Currently Amended) A semiconductor structure comprising:
a semiconductor substrate; and
a Langmuir-Blodgett chemically amplified photoresist over said substrate, said chemically amplified photoresist including a non-ionic photoacid generator bonded to the hydrophobic region of an amphipathic molecule and an acid sensitive polymer.
14. (Original) The structure of claim 13 wherein said photoacid generator is MDT.
15. (Original) The structure of claim 13 wherein said photoacid generator is NIT.